

**CIR-S3SUSG1002G**

DDR3 SO-DIMM 1066MHz 2GB

**Description**

The CIR-S3SUSG1002G is 128M words X 64 bits, 2 ranks . Unbuffered Small Outline Dual In-Line Memory Module (SO-DIMM) .DDR3 SDRAMs in Fine Ball Grid Array(FBGA) packages on a 204pin glass-epoxy substrate. Provide a high performance 8 byte interface in 67.60mm width form factor of industry standard. It is suitable for easy interchange and addition.

**Specifications**

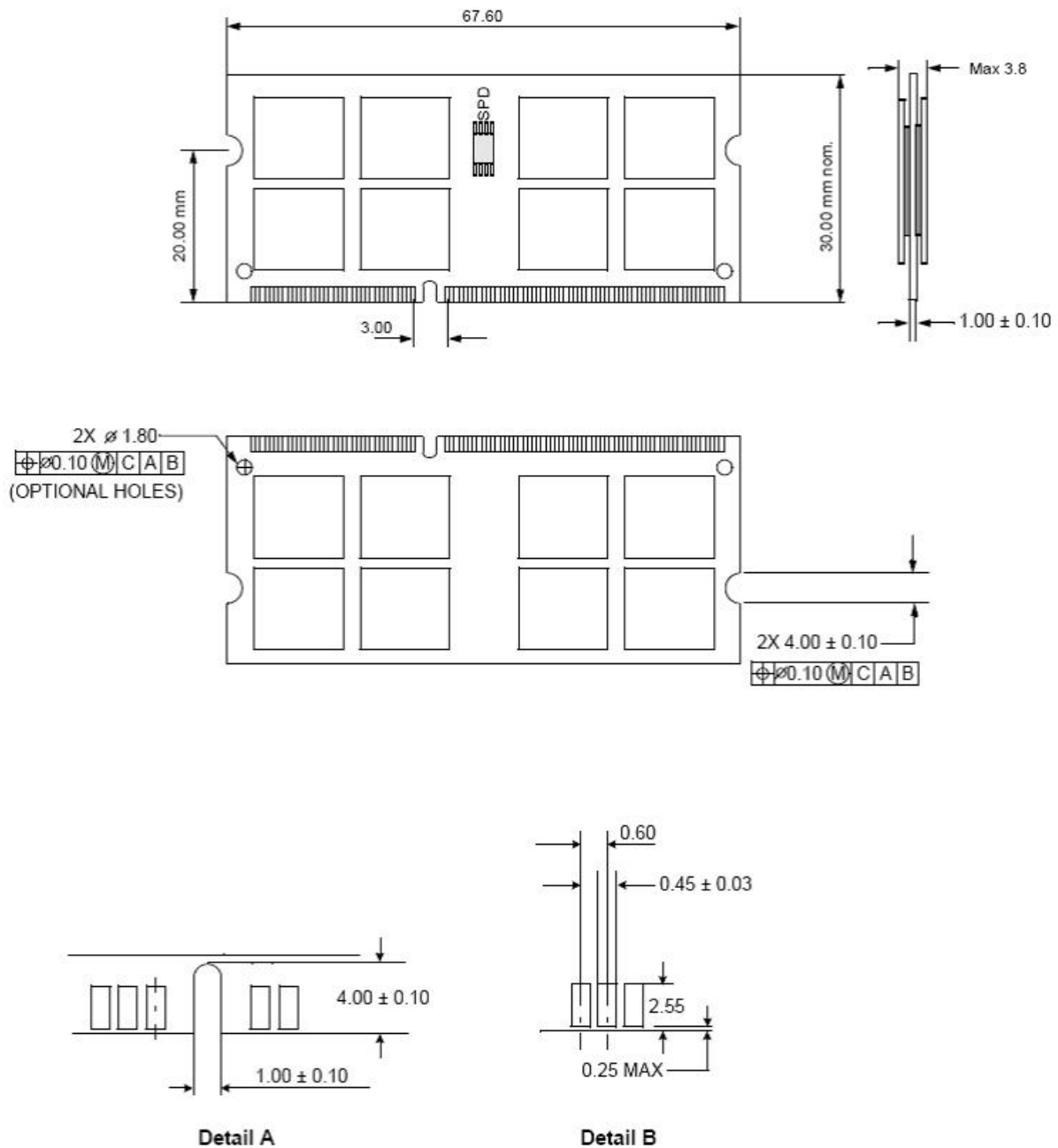
Density	2GB
Pin Count	204pin
Type	Unbuffered
Dimensions	67.6mm x 30.0mm
ECC	Non-ECC
Component Config	128M x 8 bit
Data Rate	1066 Mbps
CAS Latency	7
Voltage:	1.5V
PCB Layers	8
Operating Temp.	0°C~+85°C
Module Ranks	Dual Rank

**Features**

- Data rate:1066Mbps
- 204pin,Small outline dual in-line memory module(SO-DIMM)
- Power supply: VDD= 1.5V + 0.075V
- Interface: SSTL\_15
- Programmable CAS Latency(CL):7 support
- /CAS write latency(CWL):5,6,7,8
- Fully differential clock inputs (CK, /CK) operation
- Differential Data Strobe (DQS, /DQS)
- DM masks write data-in at the both rising and falling edges of the data strobe
- BL switch on the fly
- 8banks
- 8K refresh cycles /64ms
- Dynamic On Die Termination supported
- Asynchronous RESET pin supported
- ZQ calibration supported
- TDQS (Termination Data Strobe) supported (x8 only)
- Write Levelization supported
- Refresh: Auto-Refresh, Self-Refresh
- On Die Thermal Sensor supported(JEDEC optional)
- 8 bit pre-fetch
- Lead-Free Products are RoHS compliant
- Average Refresh Period 7.8us at  $0^{\circ}\text{C} \leq \text{TC} \leq 85^{\circ}\text{C}$

### Package Dimensions

Unit: mm



Tolerances :  $\pm 0.15$ mm unless otherwise specified